

IN THE CLAIMS:

\ Kindly amend Claim 1 as follows:

Subt B<sup>1</sup>  
1. (Amended) A lateral metal-oxide semiconductor field effect transistor (MOSFET),

A<sup>3</sup>  
comprising:

a silicon carbide layer located on or within a substrate of a semiconductor wafer, a gate  
formed on the silicon carbide layer; and

source and drain regions located in the silicon carbide layer and laterally offset from the  
gate.